

Title (en)

Silicon on insulator semiconductor device and its fabrication method.

Title (de)

Silicon auf Isolator-Halbleiteranordnung und Verfahren zur Herstellung.

Title (fr)

Dispositif semiconducteur en Silicium sur isolant et méthode pour sa fabrication.

Publication

EP 0616371 A2 19940921 (EN)

Application

EP 94104193 A 19940317

Priority

- JP 5891293 A 19930318
- JP 29767293 A 19931129
- JP 30780793 A 19931208

Abstract (en)

A semiconductor device comprises an insulating region residing adjacent to a first semiconductor region, a control electrode residing via the insulating region, a second semiconductor region and a third semiconductor region, which have an opposite conduction type to that of the first semiconductor region, residing adjacent to and carrying therebetween the first semiconductor region. When the first, second and third semiconductor regions and the control electrode are grounded, the first semiconductor region in contact with the insulating layer is adjusted to be in weak inversion state, and the potential of the control electrode and that of the first semiconductor region are electrically coupled to be operable. <IMAGE>

IPC 1-7

H01L 29/73; **H01L 29/784**; **H01L 27/12**

IPC 8 full level

H01L 21/331 (2006.01); **H01L 21/84** (2006.01); **H01L 27/06** (2006.01); **H01L 27/12** (2006.01); **H01L 29/732** (2006.01); **H01L 29/739** (2006.01)

CPC (source: EP US)

H01L 21/84 (2013.01 - EP US); **H01L 27/0623** (2013.01 - EP US); **H01L 27/1203** (2013.01 - EP US); **H01L 29/66265** (2013.01 - EP US); **H01L 29/732** (2013.01 - EP US); **H01L 29/7394** (2013.01 - EP US); **H01L 29/7395** (2013.01 - EP US)

Cited by

FR2789519A1; CN101140940A; DE19515797C1; US5846858A; US6787850B1; WO0046858A1

Designated contracting state (EPC)

DE FR GB IT NL

DOCDB simple family (publication)

EP 0616371 A2 19940921; **EP 0616371 A3 19950802**; **EP 0616371 B1 20020703**; DE 69430881 D1 20020808; DE 69430881 T2 20021107; US 5451798 A 19950919

DOCDB simple family (application)

EP 94104193 A 19940317; DE 69430881 T 19940317; US 20672994 A 19940307